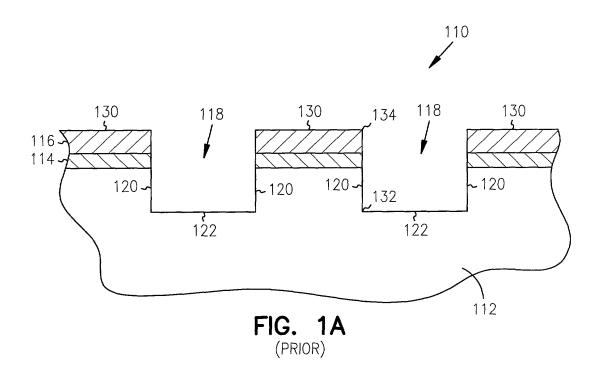
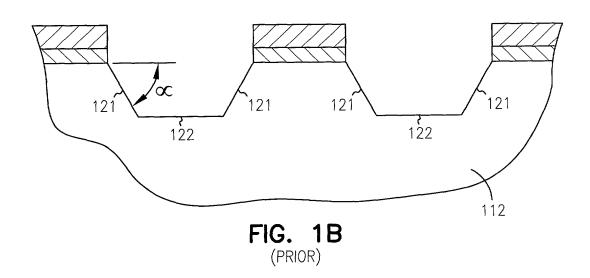
TITLE: TRANSISTOR STRUCTURE HAVING REDUCED TRANSISTOR LEAKAGE ATTRIBUTES INVENTORS NAME: Vishnu K. Agarwal et al. DOCKET NO.: 303.780US1

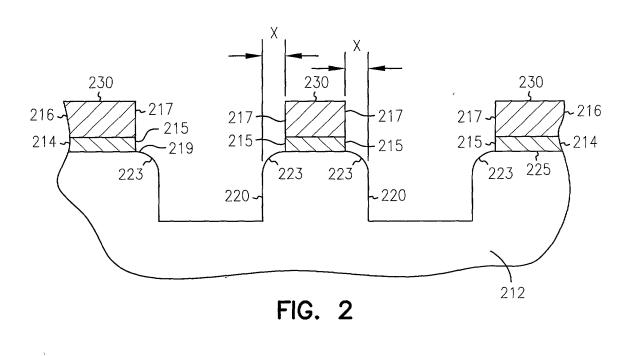
1/8

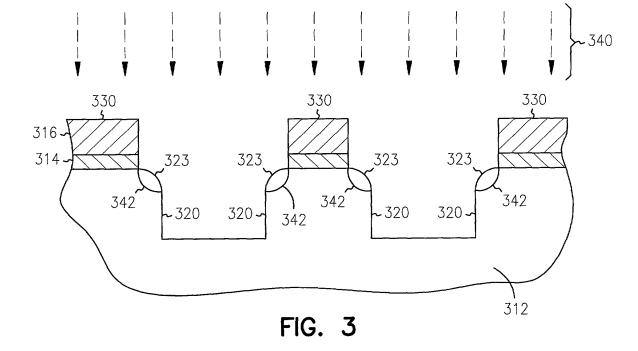




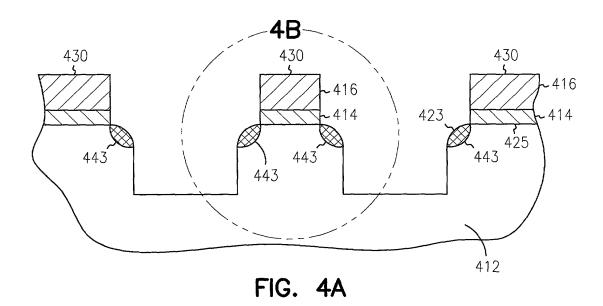
DOCKET NO.: 303.780US1

2/8





3/8



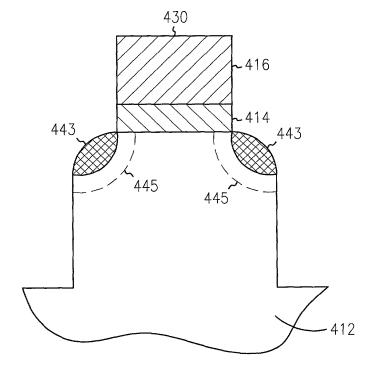


FIG. 4B

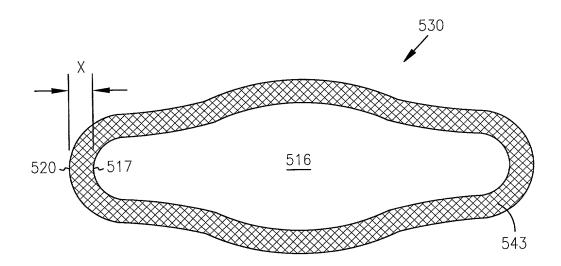
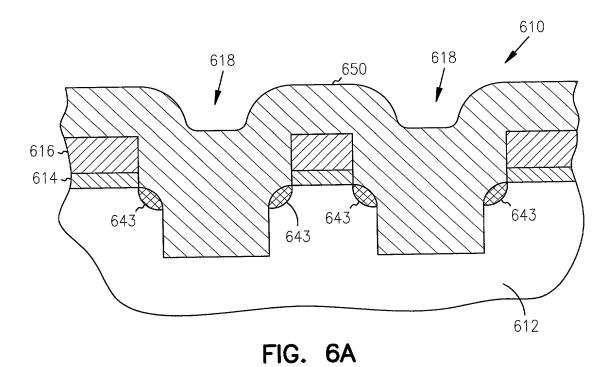


FIG. 5



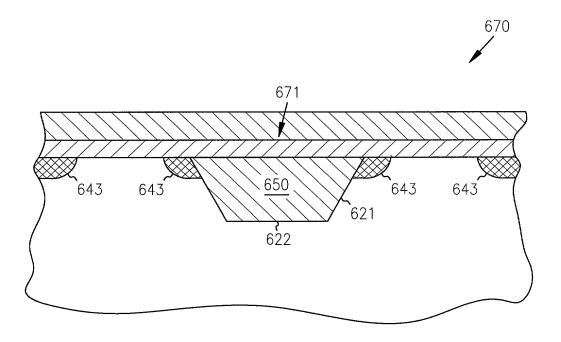


FIG. 6B

700 \_

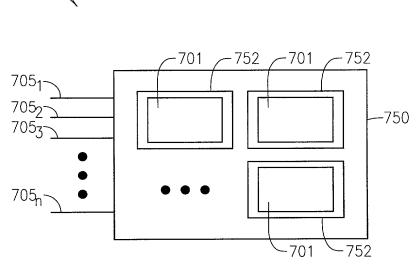


FIG. 7

gedinament i traditale a m

6/8

800~

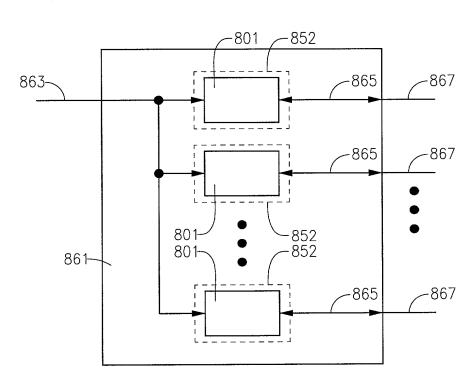


FIG. 8

900~

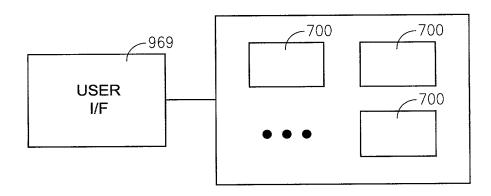
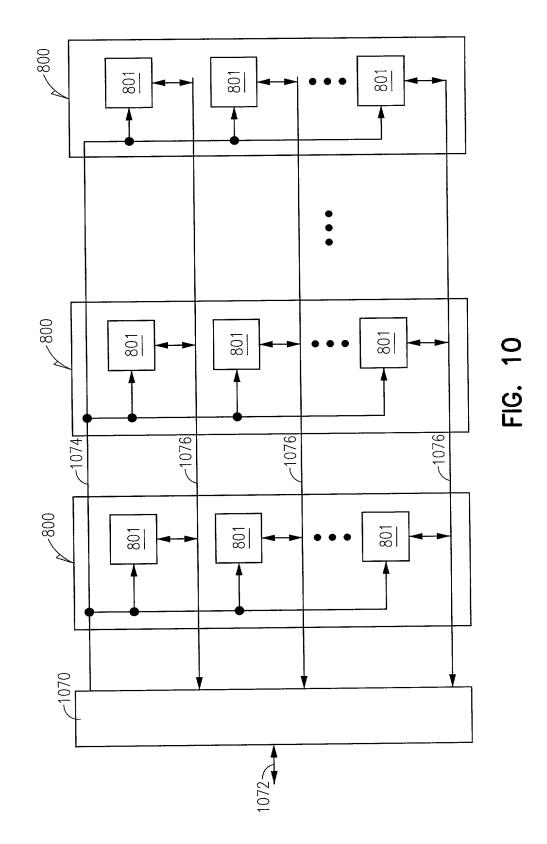


FIG. 9

A CONTRACT OF MANAGEMENT AND CONTRACTOR

en samp sy



1100~

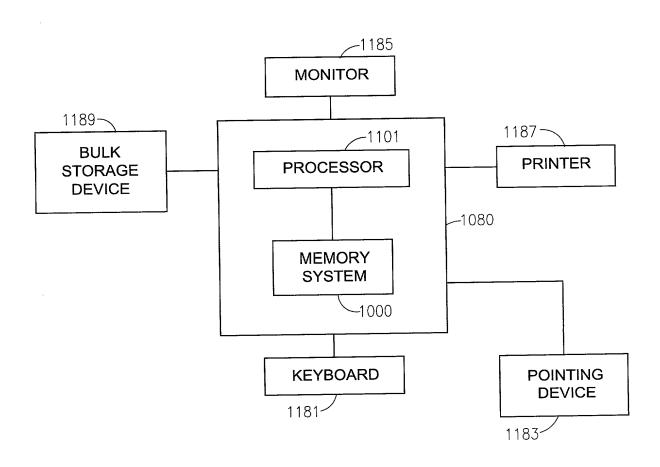


FIG. 11